

ABSTRACT OF THE DISCLOSURE

Provided are a resist material and a pattern formation method which have a good coating property, suppresses the occurrences of microbubbles in the solution and hardly generate a various kinds of defects causing a yield reduction in device step. Specifically, a resist material comprising a non-ionic surfactant containing neither a fluorine substituent nor a silicon-containing substituent in addition to a surfactant having a fluorine substituent and a pattern formation method therewith are provided.